

## **Amendments to the Specification**

Please delete the paragraph at page 1, line 1.

Please insert the following revised title at page 1, line 1:

### **METHODS FOR PRODUCING SILICON NITRIDE FILMS AND SILICON OXYNITRIDE FILMS BY THERMAL CHEMICAL VAPOR DEPOSITION**

Please insert the following paragraph at page 1, line 3:

This application claims the benefit of priority under 35 U.S.C. § 119 (a) and (b) to Japanese Application No. 2002-279880, filed September 25, 2002, the entire contents of which are incorporated herein by reference.

Please replace the subtitle at page 1, line 4, with the following replacement subtitle:

#### **~~Background of the Invention~~**

Please delete the subtitles at page 1, lines 6 and 12.

Please replace the subtitle at page 2, line 28, with the following replacement subtitle:

#### **~~Summary of the Invention~~**

Please insert the following paragraph at page 4, line 19:

The invention includes methods to achieve the desired results, as described, but is not limited to the various embodiments disclosed.

Please insert the following paragraph at page 4, line 21:

The invention includes methods to achieve the desired results, as described, but is not limited to the various embodiments disclosed.

Please delete the text at page 8, line 20, through page 9, line 11,

Please insert the following paragraph at page 17, line 13:

It will be understood that many additional changes in the details, materials, steps and arrangement of parts, which have been herein described in order to explain the nature of the invention, may be made by

those skilled in the art within the principle and scope of the invention as expressed in the appended claims. Thus, the present invention is not intended to be limited to the specific embodiments in the examples given above.

Please replace the subtitle at page 18, line 1, with the following text:

**CLAIMS** What is claimed is: